	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	ErrorDefinitio	r r o
1	BRS	44	dram and capacitor and (hsg or hemispher\$) with nitride and fill\$ with \$resist	1	2004/10/26 23:34			Ο
2	BRS	11	dram and capacitor and (hsg or hemispher\$) with nitride and fill\$ with \$resist and peroxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/20 15:54			0
3	BRS	11	dram and capacitor and (hsg or hemispher\$) with nitride and fill\$ with \$resist and peroxide and (ammonia or ammonium or nh4oh)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/20 15:55			0
4	BRS	12	dram and capacitor and (hsg or hemispher\$) with nitride with \$resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/26 23:15			0
5	BRS	44	dram and capacitor and (hsg or hemispher\$) with nitride and fill\$ with \$resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/26 23:34		***************************************	0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m	e f i n	o r
6	BRS	12 6	dram and capacitor and (hsg or hemispher\$) with nitride and \$resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/26 23:57			0
7	BRS	6	dram and capacitor and (hsg or hemispher\$ or rugg\$ or rough\$) near nitride and \$resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/26 23:59			0
8	BRS	1	rugg\$ or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/26 23:59			О
9	BRS	53	dram and capacitor and (hsg or hemispher\$ or rugg\$ or rough\$) near3 nitride and \$resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 00:01			0

	Тур	Hi ts	Search Text	DBs	Time	Stamp	m m	e f i	Errors
10	BRS	11 1	dram and capacitor and (hsg or hemispher\$ or rugg\$ or rough\$) with (cavity or trench or hole or opening) and nitride and \$resist with fill\$ with (cavity or trench or opening or hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/	10/27			0
11	BRS	22	dram and capacitor and (hsg or hemispher\$ or rugg\$ or rough\$) with (cavity or trench or hole or opening) and nitride with (hsg or hemispher\$ or rugg\$ or rough\$) and \$resist with fill\$ with (cavity or trench or opening or hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/ 13:11	10/27			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	D e f i	Error
12	BRS			JPO; DERWENT;	2004/10/27 13:27			0
13	BRS	6	dram and capacitor and (titanium adj nitride or tin) with \$resist with reces\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:34			0
14	BRS	6	dram and capacitor and (metal adj nitride or tin) with \$resist with reces\$,	2004/10/27 13:36		***************************************	0
15	BRS	9	capacitor and (metal adj nitride or tin) with \$resist with reces\$		2004/10/27 13:42		100 Marie 100 Ma	0
16	BRS		(metal adj nitride or tin) with \$resist with reces\$		2004/10/27 13:45			0

	Тур	Hi ts	Search Text	DBs 	Time Stamp	m m e	r D e f	E r r
17	BRS	17	(ammoni\$ or nh or \$chloric or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:55			О
18	BRS		nitride with \$resist with (ammoni\$ or nh or \$chloric or \$9chloride or hcl) with \$peroxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:55		700	0
19	BRS		(nitride or tin or wn or tan) with \$resist with (ammoni\$ or nh or \$chloric or \$9chloride or hcl) with \$peroxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 14:03			0
20	BRS		(nitride or tin or wn or tan) with \$resist with select\$9 with (etch\$ or reces\$) and (ammoni\$ or nh or \$chloric or \$9chloride or hcl) with \$perovide	1	2004/10/27 14:36			0
21	BRS	3	\$P\$59X5d6" "6083849" "6261964").PN.	USPAT	2004/10/27 14:25			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	r D e f	E r o r
22	BRS	75	electrode and \$resist with	I	2004/10/27 15:28			0
23	BRS	99	tin or wn or tan) with (lower or storage or bottom) with electrode and \$resist with select\$9 with (etch\$ or reces\$) and capacitor and fill\$ with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:31			0
24	BRS	1	\$resist (nitride or tin or wn or tan) near (lower or storage or bottom) near electrode and \$resist with select\$9 with (etch\$ or reces\$) and capacitor and fill\$ with \$resist		2004/10/27 15:29			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	ErrorDefinitio	E r r
25	BRS	. 66	(nitride or tin or wn or tan) with (lower or storage or bottom) with electrode and \$resist with select\$9 with (etch\$ or reces\$) and capacitor and fill\$ with \$resist with (trench or cavity or hole or recess)	1	2004/10/27 15:35			0
26	BRS		(nitride or tin or wn or tan) with (lower or storage or bottom) with electrode and \$resist with select\$9 with (etch\$ or reces\$) and capacitor and fill\$ with \$resist with (trench or cavity or hole or recess) and electrode with fill\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:37			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	f i n	o r
27	BRS	6		USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/27 15:47			Ο
28	BRS	11		USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/27 15:49			0
29	BRS	6	dram and capacitor near (container or cup or trench) and nitride near electrode and fill\$ with \$resist	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/27 15:49			0
30	BRS		cup or trench)	JPO; DERWENT;	2004/10/27 15:50			0